

0057-2533-2YY CONT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

Hideki TAKAHASHI

SERIAL NO: New Application

FILED: Herewith

FOR: INSULATED GATE SEMI-
CONDUCTOR DEVICE AND MANU-
FACTURING METHOD THEREOF

:

: EXAMINER: To be Assigned

:

: GROUP ART UNIT: To be Assigned

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified application, as follows, without prejudice:

IN THE CLAIMS

Please cancel Claims 1-21, without prejudice or disclaimer.

Please add new Claims 22-39, as follows:

*Sub B'
Cont*

figs. 3, 22, 23

22. (New) An insulated gate semiconductor device, comprising:
- a first semiconductor layer of a first conductivity type having first and second main surfaces on opposite sides thereof;
 - a second semiconductor layer of a second conductivity type provided on said first main surface of said first semiconductor layer;